

L Number	Hits	Search Text	DB	Time stamp
172	1813	high near dielectric near constant near film	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/09 07:52
173	144	(gate near (insulating or dielectric)) near10 (high near dielectric near constant near film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/09 07:53
174	9	(gate near (insulating or dielectric)) near10 (high near dielectric near constant near film) and (metal near2 oxygen near2 silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/09 08:00
175	4	(gate near (insulating or dielectric)) near10 (high near dielectric near constant near film) and (metal near2 oxygen near2 silicon).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/09 08:05
176	4	(gate near (insulating or dielectric)) near10 (metal near2 oxygen near2 silicon).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/09 08:07
177	8	(gate near (insulating or dielectric)) near10 (metal near2 (oxide or oxygen) near2 silicon).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/09 08:09
178	5	(gate near (insulating or dielectric)) near10 (metal near2 (oxide or oxygen) near2 silicon) near10 nitrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/09 08:09
179	2	((gate near (insulating or dielectric)) near10 (metal near2 (oxide or oxygen) near2 silicon) near10 nitrogen) and (high near dielectric near constant)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/09 08:10
180	14	(high near dielectric near constant near film) near10 (barrier near film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/09 08:11
181	3	((high near dielectric near constant near film) near10 (barrier near film)) and ((barrier near film) near5 nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/09 08:12

182	12	((high near dielectric near constant near (layer or film)) near10 (barrier near (layer or film))) and ((barrier near (layer or film)) near5 nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/09 08:14
183	6	((high near dielectric near constant near (layer or film)) near10 (barrier near (layer or film))) and ((barrier near (layer or film)) near5 nitrogen).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/09 08:16
184	20	((high near dielectric near constant near (layer or film)) near10 (barrier near (layer or film))) and ((barrier near (layer or film)) near5 (nitride or nitrogen)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/09 08:16
185	3	((high near dielectric near constant near (layer or film)) near10 (barrier near (layer or film))) and ((barrier near (layer or film)) near5 (nitride or nitrogen) near5 (oxy or oxygen)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/09 08:17
186	12	((high near dielectric near constant near (layer or film)) near10 (barrier near (layer or film))) and ((barrier near (layer or film)) near5 (metal and oxygen and silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/09 08:20
187	9	metal near oxygen near silicon near nitrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/09 08:41

L Number	Hits	Search Text	DB	Time stamp
203	6	((gate adj (insulating or dielectric)) near10 (high near dielectric near constant near (layer or film)) near10 silicon).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/09 09:15
204	6	((gate adj (insulating or dielectric)) near10 (high near dielectric near constant near (layer or film)) near10 silicon).clm.) and (high near dielectric near constant near (film or layer)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/09 09:15